

KIENZLE - INNOVATION WORLD

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五、六、七、八、九、十、十一、十二、十三、十四、十五

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中国历代书画作品集

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1 Active
2 L1: (9595) (floating adj gate).clm. or (control adj gate).clm.
3 L2: (1517) 1 and (spacer\$1.clm. or sidewall\$1.clm.)
4 L3: (1380) 2 and (floating adj gate).clm.
5 L4: (1351) 3 and ((oxide or polysilicon or (non adj nitride)) near10_gate)
6 L5: (1086) 3 and ((oxide or polysilicon or (non adj nitride)) near6 (spacers\$1 or sidewall\$1))
7 L6: (830) 5 and (spacer\$1 or sidewall\$1) near10 (floating adj gate))
8 L7: (817) 6 and (spacer\$1 or sidewall\$1) near8 (floating adj gate))
9 L8: (579) 6 and ((spacer\$1 or sidewall\$1) near8 (floating adj gate)).clm.
10 L9: (552) 8 and ((spacer\$1 or sidewall\$1) near5 (oxide or polysilicon or (non adj nitride)))
11 L10: (310) 8 and ((spacers\$1 or sidewall\$1) near5 (oxide or polysilicon or (non adj nitride))).
12 L11: (201) 10 and transistor
13 L12: (159) 11 and (transistor or source or drain).clm.
14 L13: (200) 11 and (memory or (non adj volatile))
15 L14: (184) 13 and (memory.clm. or (non adj volatile).clm. or transistor.clm.)
16 L15: (157) 14 and floating.clm. and control.clm.
17 L16: (145) 15 and ((memories or memory or (non adj volatile)).clm. or (transistor and capacito
18 L17: (145) 16 and (memories or memory or (non adj volatile)).clm.
19 L18: (74) 17 and (nitride near10 (spacer\$1 or sidewall))

17 and (nitride with
(spacerS1 or sidewall))

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Serial	Category	Document ID	Issue Date	Pages	Title	Current OR	Current I1	Next I1	Inventor	C	C	C	C
30	P	US 20010000153	20010405	9	Double sidewall short channel split gate flash	438/257	257/E21.68		Ogura, Seiki	✓	✓	✓	✓
31	P	US 6774431	20040810	17	High coupling floating B2		257/316	257/315	Rudeck, Paul	✓	✓	✓	✓
32	P	US 6765258	20040720	18	Stack-gate flash memory B1	257/315			Wu, Ching-Yuan	✓	✓	✓	✓
33	P	US 6756631	20040629	18	Stacked-gate cell B2	257/316	257/317	257/319	Wu, Ching-Yuan	✓	✓	✓	✓
34	P	US 6746918	20040608	26	Methods of fabricating a stack-gate non-volatile B2	438/257	438/201	438/211	Wu, Ching-Yuan	✓	✓	✓	✓
35	P	US 6734055	20040511	13	Multi-level (4 state/2-bit) stacked ca B1	438/201	438/211	438/258	Lin, Chrong Jung et al.	✓	✓	✓	✓
36	P	US 6720219	20040413	9	Split gate flash memory B2	438/264	438/257	438/259	Huang, Tsai-Yu	✓	✓	✓	✓
37	P	US 6716703	20040406	21	Method of making a semiconductor memory de B2	438/264	438/267	438/596	Hoshimoto, Hiroshi	✓	✓	✓	✓
38	P	US 6690059	20040210	23	Self-aligned multi-bit flash memory cell and i B2	257/316	257/390	257/401	Wu, Ching-Yuan	✓	✓	✓	✓
39	P	US 6689658	20040210	24	Methods of fabricating a stack-gate flash memo B2	438/257	257/315	257/321	Wu, Ching-Yuan	✓	✓	✓	✓
40	P	US 6653183	20031125	9	Method of forming poly tip of floating gate in B1	438/257	257/E21.20	91	Huang, Yung-Meng et al.	✓	✓	✓	✓
41	P	US 6570213	20030527	22	Self-aligned split-gate	257/315	257/314		Wu, Ching-Yuan	✓	✓	✓	✓